a lateral metal-oxide semiconductor field effect transistor (MOSFET), including:

a silicon carbide tub located within a trench formed in a conductive substrate;

a gate formed on the silicon carbide tub; and

source and drain regions located in the silicon carbide tub and laterally offset from the gate; and

a complimentary metal-oxide semiconductor (CMOS) device formed on the conductive substrate, the CMOS device having a tub comprising a material different from the silicon carbide tub.

(2) Please cancel Claims 11-43 and 48 without prejudice or disclaimer.

(3) Please add new Claim 54 as follows:

--54. (New) A semiconductor device, comprising:

a lateral metal-oxide semiconductor field effect transistor (MOSFET), including:

a silicon carbide tub located within or contacting a conductive substrate;

a gate formed on the silicon carbide tub; and

source and drain regions located in the silicon carbide tub and laterally offset from the gate; and

a complimentary metal-oxide semiconductor (CMOS) device formed on the conductive substrate, the CMOS device having a tub comprising a material different from the silicon carbide tub, and wherein the conductive substrate includes a buried oxide layer formed therein.--